



# **isc Silicon NPN Darlington Power Transistor**

## **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 100V(Min)
- · High DC Current Gain-
- :  $h_{FE}$ = 2000(Min)@ ( $V_{CE}$ = 2V,  $I_{C}$ = 2A)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

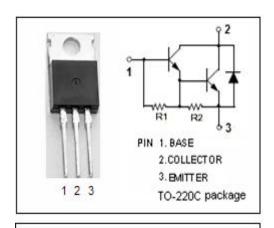


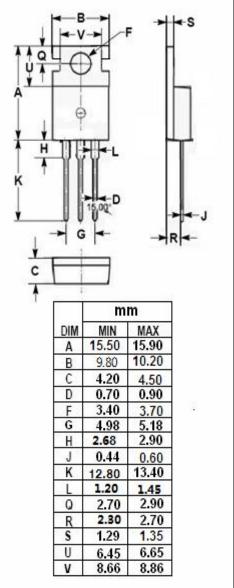
### **APPLICATIONS**

 Designed for low frequency power amplifiers and low speed switching applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	100	V	
Vceo	Collector-Emitter Voltage	V		
V <sub>EBO</sub>	Emitter-Base Voltage 7		V	
Ic	Collector Current-Continuous 5		А	
I <sub>CM</sub>	Collector Current-Peak 10		Α	
I <sub>B</sub>	Base Current-Continuous	0.5	Α	
P <sub>C</sub>	Collector Power Dissipation @T <sub>a</sub> =25℃	2	W	
	Collector Power Dissipation @T <sub>C</sub> =25℃	30	VV	
TJ	Junction Temperature	150	$^{\circ}\mathbb{C}$	
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$	







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2SD1565

### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 2mA			1.5	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 2mA			2.0	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			1.0	μА		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			3	mA		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 2V	2000		20000			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 2V	500					
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1MHz		60		pF		
f <sub>⊤</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V		80		MHz		
Switching Times								
ton	Turn-on Time			1.0		μ <b>S</b>		
t <sub>stg</sub>	Storage Time	$\begin{array}{l} I_{\text{C}}\text{= 2A, }I_{\text{B1}}\text{= }I_{\text{B2}}\text{= 2mA,} \\ V_{\text{CC}}\approx \ 50\text{V; }R_{\text{L}}\text{= 25}\Omega \end{array}$		3.5		μ <b>S</b>		
t <sub>f</sub>	Fall Time			1.2		μS		

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